Supplementary Material: Absence of backscattering in Fermi–arc–mediated conductivity of topological Dirac semimetal Cd₃As₂

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Supplementary Note 1: Refined Two–Orbital Tight–Binding Model for Cd₃As₂

For a general 2x2 Hamiltonian

$$H_{ab}(\mathbf{k}) = \left[\begin{array}{cc} h_{1\mathbf{k}} & v_{\mathbf{k}} \\ v_{\mathbf{k}}^* & h_{2\mathbf{k}} \end{array} \right],$$

the eigenvalues are given by

$$h_{1,2}(\mathbf{k}) = \frac{h_{1\mathbf{k}} + h_{2\mathbf{k}}}{2} \mp \frac{1}{2}\sqrt{(h_{1\mathbf{k}} - h_{2\mathbf{k}})^2 + 4|v_{\mathbf{k}}|^2}.$$

If we start from the LDA band structure of Cd₃As₂, we have two dispersive bands, therefore

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$$\epsilon_2(\mathbf{k}) - \epsilon_1(\mathbf{k}) = \sqrt{(h_{1\mathbf{k}} - h_{2\mathbf{k}})^2 + 4|v_{\mathbf{k}}|^2}.$$

To determine tight binding parameters, we use the following lattice translations of the body centered tetragonal lattice (in units of lattice constants a, a, c along x,y,z axis)

$$\begin{array}{rcl} A & = & (1,0,0), \\ B & = & (0,1,0), \\ C & = & (1/2,1/2,1/2) \end{array}$$

Nearest neighbor vectors from the origin are the following:

Denote $\epsilon_0 = h(0), t_i = h(R_i)$. Generally, for $h(k_x, k_y, k_z)$ obeying full lattice symmetry, we expect that

$$\begin{split} h(k_x,k_y,k_z) &= \sum_{R} e^{ik_x R_x} e^{ik_y R_y} e^{ik_z R_z} h(R_x,R_y,R_z) = \\ &\quad \epsilon_0 + t_1 (e^{ik_x a} + e^{-ik_x a} + e^{ik_y a} + e^{-ik_y a}) + \\ &\quad t_2 (e^{ik_x a/2} e^{ik_y a/2} e^{ik_z a/2} + \ldots) + t_3 (e^{ik_z a} + e^{-ik_z a}) \\ &\quad + t_4 (e^{ik_x a/2} e^{ik_y a/2} + e^{ik_x a/2} e^{-ik_y a/2} + e^{-ik_x a/2} e^{ik_y a/2} + e^{-ik_x a/2} e^{-ik_y a/2}) + \ldots \\ &= \epsilon_0 + 2t_1 (\cos k_x a + \cos k_y a) + \\ &\quad 8t_2 \cos k_x a/2 \cos k_y a/2 \cos k_z a/2 + \ldots \end{split}$$

According to the $k \cdot p$ result, we do not anticipate dispersion of $v_{\mathbf{k}}$ along 001 line because $v_{\mathbf{k}} = \lambda(k_x + ik_y)$. As as result,

$$H_{ab}(0,0,k_z) = \begin{bmatrix} h_{1\mathbf{k}} & 0\\ 0 & h_{2\mathbf{k}} \end{bmatrix},$$

and

$$\begin{aligned} \epsilon_1(0,0,k_z) &= h_1(0,0,k_z), \\ \epsilon_2(0,0,k_z) &= h_2(0,0,k_z). \end{aligned}$$

Thus, the dispersion along 001 determines $h(0, 0, k_z)$

Denoting $t_i = h(R_i)$ we obtain along 001 direction:

$$h(0,0,k_z) = \sum_{R} e^{ik_z R_z} h(R_x, R_y, R_z) = \epsilon_0 + 4t_1 + 8t_2 \cos k_z a/2 + 2t_3 \cos k_z a + 4t_4 + 8t_5 \cos k_z a + 16t_6 \cos k_z a/2 + 8t_7 \cos k_z a = \epsilon_0 + 4(t_1 + t_4) + 8(t_2 + 2t_6) \cos k_z a/2 + 2(t_3 + 4t_5 + 4t_7) \cos k_z a + \dots$$

For the $\mathbf{k} = (0, 0, 0) 2\pi/a$

$$h(0,0,0) = \epsilon_0 + 4(t_1 + t_4) + 8(t_2 + 2t_6) + 2(t_3 + 4t_5 + 4t_7)$$

For the $\mathbf{k} = (0, 0, 1)2\pi/a$

$$h(0,0,1) = \epsilon_0 + 4(t_1 + t_4) - 8(t_2 + 2t_6) + 2(t_3 + 4t_5 + 4t_7).$$

For the $\mathbf{k} = (0, 0, 1/2)2\pi/a$

$$h(0, 0, 1/2) = \epsilon_0 + 4(t_1 + t_4) - 2(t_3 + 4t_5 + 4t_7).$$

For the $\mathbf{k} = (0, 0, 1/4) 2\pi/a$

$$h(0, 0, 1/4) = \epsilon_0 + 4(t_1 + t_4) + 8(t_2 + 2t_6)/\sqrt{2}$$

For the $\mathbf{k} = (0, 0, 3/4)2\pi/a$

$$h(0, 0, 3/4) = \epsilon_0 + 4(t_1 + t_4) - 8(t_2 + 2t_6)/\sqrt{2}$$

We obtain the following connections between hopping integrals:

$$\begin{aligned} \epsilon_0 + t_1 + t_4 &= \left[h(0,0,0) + h(0,0,1) + 2h(0,0,1/2)\right]/16, \\ t_2 + 2t_6 &= \left[h(0,0,0) - h(0,0,1)\right]/16, \\ t_3 + 4t_5 + 4t_7 &= \left[h(0,0,0) + h(0,0,1) - 2h(0,0,1/2)\right]/8, \\ \epsilon_0 + t_1 + t_4 &= \left[h(0,0,1/4) + h(0,0,3/4)\right]/8, \\ t_2 + 2t_6 &= \left[h(0,0,1/4) - h(0,0,3/4)\right]\sqrt{2}/16, \end{aligned}$$

We now interpret the above described two orbital model as the two LDA energy bands that cross the Fermi level and produce the Dirac point along $\Gamma - Z$ line of the Brillouin Zone. We can interpreted these two orbitals in the spinor basis of $|\uparrow\rangle$ and $|\downarrow\rangle$ states. We use the LDA extracted values for the first band

$$\begin{aligned} \epsilon_1(0,0,0) &= 0.02eV, \\ \epsilon_1(0,0,1) &= -0.41eV, \\ \epsilon_1(0,0,1/2) &= -0.09eV, \\ \epsilon_1(0,0,1/4) &= -0.01eV, \\ \epsilon_1(0,0,3/4) &= -0.24eV, \end{aligned}$$

which produces

$$\begin{split} \epsilon_0^{(1)}/4 + t_1^{(1)} + t_4^{(1)} &= -0.0356 eV, \\ t_2^{(1)} + 2t_6^{(1)} &= +0.0269 eV, \\ t_3^{(1)} + 4t_5^{(1)} + 4t_7^{(1)} &= -0.0262 eV. \end{split}$$

We need to use $\epsilon_0^{(1)} > 0$ so that there is gap everywhere in the BZ except the Dirac point. This gives us the set of on–site energies and hopping integrals for the first orbital:

$$\begin{array}{rcl} \epsilon_{0}^{(1)} &=& 0.1 eV, \\ t_{1}^{(1)} &=& -0.0606 eV, \\ t_{2}^{(1)} &=& 0.0269 eV, \\ t_{3}^{(1)} &=& -0.0262 eV, \end{array}$$

Similarly, we use the LDA extracted values for the second band:

$$\begin{aligned} \epsilon_2(0,0,0) &= -0.02eV, \\ \epsilon_2(0,0,1) &= 0.55eV, \\ \epsilon_2(0,0,1/2) &= 0.35eV, \\ \epsilon_2(0,0,1/4) &= 0.05eV, \\ \epsilon_2(0,0,3/4) &= 0.50eV, \end{aligned}$$

$$\begin{aligned} \epsilon_0^{(2)}/4 + t_1^{(2)} + t_4^{(2)} &= +0.0769 eV, \\ t_2^{(2)} + 2t_6^{(2)} &= -0.0356 eV, \\ t_3^{(2)} + 4t_5^{(2)} + 4t_7^{(2)} &= -0.0212 eV. \end{aligned}$$

We need to use $\epsilon_0^{(2)} < 0$ for the fit so that there is gap everywhere in the BZ except the Dirac point. This gives the second set of on–site energies and hopping integrals for the second orbital:

$$\begin{array}{rcl} \epsilon_{0}^{(2)} &=& -0.1 eV \\ t_{1}^{(2)} &=& 0.1019 eV \\ t_{2}^{(2)} &=& -0.0356 eV \\ t_{3}^{(2)} &=& -0.0212 eV \end{array}$$

Finally in $k \cdot p$ theory, the off-diagonal parameter between first (spin up) and second (spin down) orbitals $v(\mathbf{k}) = \lambda(k_x + ik_y)$. The tight-binding representation that leads to this

$$\begin{aligned} v(\mathbf{k}) &= \sum_{R} e^{i\mathbf{k}\mathbf{R}} v(\mathbf{R}) = v(100)e^{ik_{x}} + v(-100)e^{-ik_{x}} + v(010)e^{ik_{y}} + v(0-10)e^{-ik_{y}} + \\ &\quad v(200)e^{ik_{x}} + v(-200)e^{-ik_{x}} + v(020)e^{ik_{y}} + v(0-20)e^{-ik_{y}} \\ &= \lambda_{1}(e^{ik_{x}} - e^{-ik_{x}})/2i + \lambda_{1}i(e^{ik_{x}} - e^{-ik_{x}})/2i + \\ &\quad \lambda_{11}(e^{ik_{x}}e^{ik_{y}} - e^{ik_{x}}e^{-ik_{y}} - e^{-ik_{x}}e^{ik_{y}} + e^{-ik_{x}}e^{-ik_{y}})/(2i)^{2} \\ &\quad \lambda_{2}(e^{i2k_{x}} - e^{-i2k_{x}})/2i + \lambda_{2}i(e^{i2k_{x}} - e^{-i2k_{x}})/2i \\ &= \lambda_{1}(\sin k_{x} + i\sin k_{y}) + \lambda_{2}(\sin 2k_{x} + i\sin 2k_{y}). \end{aligned}$$

Here we used

v(+100) v(-100) v(0+10) v(0-10)	 	$\begin{split} &+\lambda_{1}/(2i),\\ &-\lambda_{1}/(2i),\\ &+\lambda_{1}i/(2i),\\ &-\lambda_{1}i/(2i), \end{split}$
v(+200) v(-200)	=	$+\lambda_2/(2i),\\ -\lambda_2/(2i),$
v(0+20) $v(0-20)$	=	$+\lambda_2 i/(2i), \\ -\lambda_2 i/(2i).$



Figure 1: Electronic structure of the distorted Cd_3As_2 that shows a gap opening in the vicinity of Dirac points and results in a weak topological insulator phase.

The best fit is obtained with the use of the parameters:

$$\lambda_1 = -0.24eV,$$

$$\lambda_2 = +0.08eV.$$

The above parameters are used in our tight-binding simulations of the surface states and the transport properties described in text.

Supplementary Note 2: Inversion Broken Distorted Structure along (110)

Here we want to describe a symmetry broken phase as caused by a perturbation along 110 crystallographic line. It could be due to the presence of the contact in an experimental setup or strong electric field applied along (110). Such perturbation will break the inversion and leave only 4 symmetry operations of the crystalline group including 180 degrees rotation along (110) as well as reflections within basal and (1-10) planes. Our density functional LDA calculation for such symmetry broken phase involves moving the atoms of Cd and As in the opposite direction along (110) to simulate a compatible distortion. The result is plotted on Fig. 1 where one can see a small gap opening in the vicinity of the Dirac point.

We next analyze this result in terms of a generic $k \cdot p$ model. For the Dirac semimetal, such model has been described many times in the literature (see, e.g., Phys. Rev. B 88, 125427 (2013)). It consists of two orbitals with k dispersions $\pm M(\mathbf{k})$, where $M(\mathbf{k}) = M_0 - M_1(k_x^2 + k_y^2) - M_2k_z^2$, that interact via the matrix element $A(k_x \pm ik_y)$. The parameters M_0, M_1, M_2 should be chosen negative to reproduce band inversion. The model naturally respects all symmetry operations of the tetragonal lattice as is the case of the undistorted tetragonal $(I4_1/acd, No.142)$] structure of Cd₃As₂.

The lowest order $k \cdot p$ Hamiltonian that illustrates this scenario reads

$$H(\mathbf{k}) = \begin{bmatrix} +M(\mathbf{k}) & A(k_y + ik_x) & 0 & Bk_z \\ A(k_y - ik_x) & -M(\mathbf{k}) & Ck_z & 0 \\ 0 & Ck_z & +M(\mathbf{k}) & -A(k_y - ik_x) \\ Bk_z & 0 & -A(k_y + ik_x) & -M(\mathbf{k}) \end{bmatrix}$$

It describes the transition between Dirac semimetal (B = C = 0) and topological insulator $(B, C \neq 0)$ phases. If we keep off-diagonal parameters B and C different, this describes lifting of the degeneracy along ΓZ (001) line of the BZ as seen in our density functional calculation given in Figure 1.

Next, we convert this $k \cdot p$ Hamiltonian to the refined four orbital tight-binding model. However, the diagonal 2x2 subblocks of this Hamiltonian translate to the two-orbital tight-binding model that we already discussed for the Dirac semimetal phase in the previous section. The off-diagonal terms (the ones with the coefficients C and D) are periodized with the substitution of $k_z \rightarrow \sin k_z c$. The numbers C and D are small and describe the perturbation that gap the Dirac points and result in the weak topological insulator state of Cd₃As₂. We use its actual values C = D = 0.0068 eV for the plots presented in the main text.